

## SILICON EPITAXIAL PLANAR DIODE

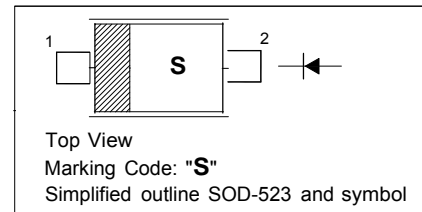
### Band Switching Diode

#### Applications

- For VHF tuner band RF attenuator
- AGC for FM tuner

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	V
Forward Current	$I_F$	50	mA
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_R$	50	-	-	V
Reverse Current at $V_R = 50\text{ V}$	$I_R$	-	-	0.1	$\mu\text{A}$
Total Capacitance at $V_R = 50\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	-	0.25	-	pF
Series Resistance at $I_F = 5\text{ mA}$ , $f = 100\text{ MHz}$	$r_s$	-	1.5	-	$\Omega$

Fig. 1  $I_c-T_a$

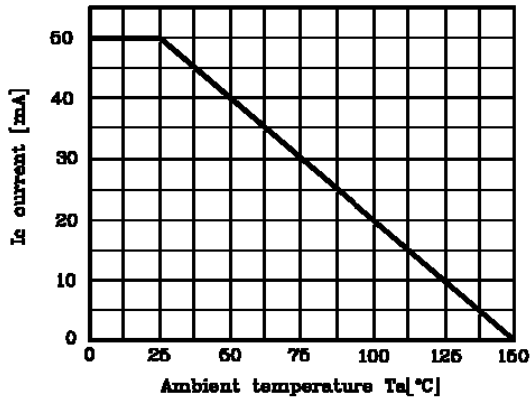


Fig. 2  $I_F-V_F$



Fig. 3  $C_T-V_R$

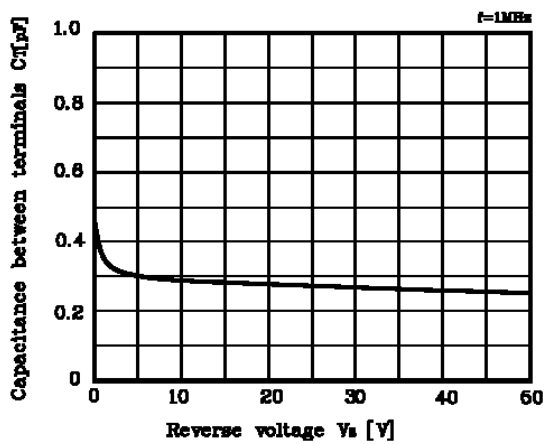


Fig. 4  $r_s-I_F$

